Fabian Thome

List of Publications by Year
in descending order

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34	405	933447 10	940533 16
papers	citations	h-index	g-index

34	34	34	295
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Comparison of a 35-nm and a 50-nm gate-length metamorphic HEMT technology for millimeter-wave low-noise amplifier MMICs. , 2017, , .		29
2	Broadband High-Power W-Band Amplifier MMICs Based on Stacked-HEMT Unit Cells. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 1312-1318.	4.6	29
3	Highly Isolating and Broadband Single-Pole Double-Throw Switches for Millimeter-Wave Applications Up to 330 GHz. IEEE Transactions on Microwave Theory and Techniques, 2018, 66, 1998-2009.	4.6	29
4	First Demonstration of Distributed Amplifier MMICs With More Than 300-GHz Bandwidth. IEEE Journal of Solid-State Circuits, 2021, 56, 2647-2655.	5.4	24
5	W-band SPDT switches in planar and tri-gate 100-nm gate-length GaN-HEMT technology. , 2018, , .		20
6	Limitations and Implementation Strategies of Interstage Matching in a 6-W, 28â€“38-GHz GaN Power Amplifier MMIC. IEEE Transactions on Microwave Theory and Techniques, 2021, 69, 2541-2553.	4.6	18
7	W-Band LNA MMICs Based on a Noise-Optimized 50-nm Gate-Length Metamorphic HEMT Technology. , 2019, , .		17
8	Low-Loss Millimeter-Wave SPDT Switch MMICs in a Metamorphic HEMT Technology. IEEE Microwave and Wireless Components Letters, 2020, 30, 197-200.	3.2	17
9	A 50-nm Gate-Length Metamorphic HEMT Technology Optimized for Cryogenic Ultra-Low-Noise Operation. IEEE Transactions on Microwave Theory and Techniques, 2021, 69, 3896-3907.	4.6	17
10	A Wideband E/W-Band Low-Noise Amplifier MMIC in a 70-nm Gate-Length GaN HEMT Technology. IEEE Transactions on Microwave Theory and Techniques, 2022, 70, 1367-1376.	4.6	17
11	Stability Investigation of Large Gate-Width Metamorphic High Electron-Mobility Transistors at Cryogenic Temperature. IEEE Transactions on Microwave Theory and Techniques, 2016, 64, 3139-3150.	4.6	16
12	Millimeter-Wave Single-Pole Double-Throw Switches Based on a 100-nm Gate-Length AlGaN/GaN-HEMT Technology. , 2019, , .		16
13	Prospects and Limitations of Stacked-FET Approaches for Enhanced Output Power in Voltage-Controlled Oscillators. IEEE Transactions on Microwave Theory and Techniques, 2016, 64, 836-846.	4.6	13
14	Comparison of two W-band low-noise amplifier MMICs with ultra low power consumption based on 50nm InGaAs mHEMT technology. , 2013, , .		12
15	InGaAs MOSHEMT W-Band LNAs on Silicon and Gallium Arsenide Substrates. IEEE Microwave and Wireless Components Letters, 2020, 30, 1089-1092.	3.2	12
16	Novel destructive-interference-envelope detector for high data rate ASK demodulation in wireless communication receivers. , 2015, , .		11
17	A 75â€“305-GHz Power Amplifier MMIC With 10â€“14.9-dBm P_{out} in a 35-nm InGaAs mHEMT Technology. IEEE Microwave and Wireless Components Letters, 2021, 31, 741-743.	3.2	11
18	A 67â€“116-GHz Cryogenic Low-Noise Amplifier in a 50-nm InGaAs Metamorphic HEMT Technology. IEEE Microwave and Wireless Components Letters, 2022, 32, 430-433.	3.2	10

#	Article	IF	Citations
19	A 50-nm gate-length metamorphic HEMT distributed power amplifier MMIC based on stacked-HEMT unit cells. , 2017, , .		9
20	Highly linear 90-170 GHz SPDT Switch with High Isolation for Fully Integrated InP Transceivers. , 2019, , .		9
21	A Scalable Small-Signal and Noise Model for High-Electron-Mobility Transistors Working Down to Cryogenic Temperatures. IEEE Transactions on Microwave Theory and Techniques, 2022, 70, 1097-1110.	4.6	9
22	An investigation of millimeter wave switches based on shunt transistors including SPDT SWITCH MMICs up to 300 GHz. , 2016, , .		8
23	A millimeter-wave low-noise amplifier MMIC with integrated power detector and gain control functionality. , 2016, , .		7
24	Planar Zero Bias Schottky Diodes on an InGaAs Metamorphic HEMT MMIC Process. IEEE Microwave and Wireless Components Letters, 2014, 24, 860-862.	3.2	6
25	70-116-GHz LNAs in 35-nm and 50-nm Gate-Length Metamorphic HEMT Technologies for Cryogenic and Room-Temperature Operation. , 2018, , .		6
26	Noise Performance of Sub-100-nm Metamorphic HEMT Technologies. , 2020, , .		6
27	Frequency Multiplier and Mixer MMICs Based on a Metamorphic HEMT Technology Including Schottky Diodes. IEEE Access, 2020, 8, 12697-12712.	4.2	6
28	Architecture of Highly Integrated Cryogenic Active Planar OrthoMode Transducer for the 3-mm Band. , 2018, , .		5
29	Low-power wireless data transmitter MMIC with data rates up to 25 Gbit/s and 9.5mW power consumption using a 113 GHz carrier. , 2014, , .		4
30	A Fully-Integrated W-Band I/Q-Down-Conversion MMIC for Use in Radio Astronomical Multi-Pixel Receivers. , 2020, , .		4
31	A W-band wireless communication transmitter utilizing a stacked-FET oscillator for high output power performance. , 2016, , .		3
32	Compact Dual-Polarization Cryogenic Receiver Module for the 75-116 GHz band. , 2018, , .		2
33	C-Band Low-Noise Amplifier MMIC with an Average Noise Temperature of 44.5 K and 24.8 mW Power Consumption. , 2022, , .		2
34	A 1â€“170-GHz Distributed Down-Converter MMIC in 35-nm Gate-Length InGaAs mHEMT Technology. IEEE Microwave and Wireless Components Letters, 2022, 32, 748-751.	3.2	1